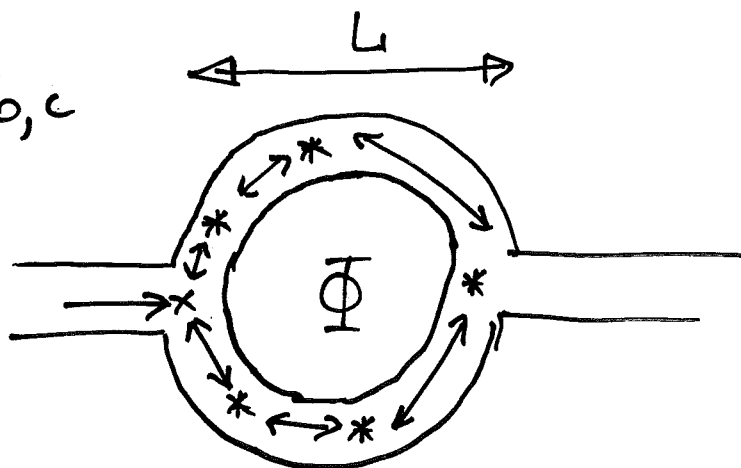


Answers Exam Mesoscopic Physics

0-7-2015

(A)

1 a, b, c



Type 1: time reversed trajectories

$$\text{AB phase: } \Delta\varphi_{\text{CW}} = 2\pi \frac{\Phi}{\Phi_0} \text{ (clockwise)}$$

$$\Phi_0 = h/e \quad \Delta\varphi_{\text{ACW}} = -2\pi \frac{\Phi}{\Phi_0} \text{ (anticlockwise)}$$

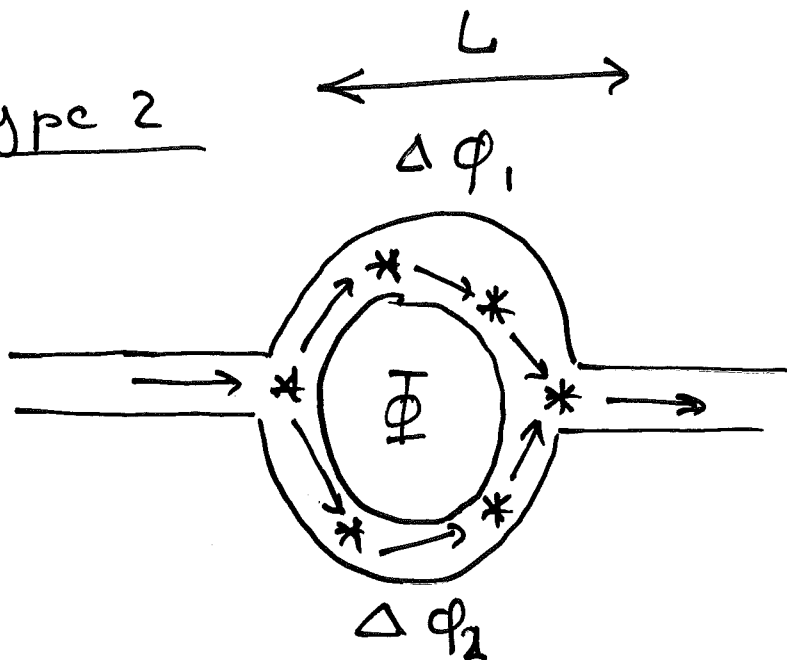
$$\text{periodicity} = \frac{h}{2e}$$

$$\text{required: } L < l_\varphi$$

voltage and temperature should be such that $L < l_\varphi$

Type 2

(B)



AB phase : $\Delta\phi_1 - \Delta\phi_2 = 2\pi \frac{\Phi}{\Phi_0}$

interference at output depends on

$$\Delta\phi_1 - \Delta\phi_2 \sim 2\pi \frac{\Phi}{\Phi_0}$$

periodicity = $\Phi_0 = h/e$

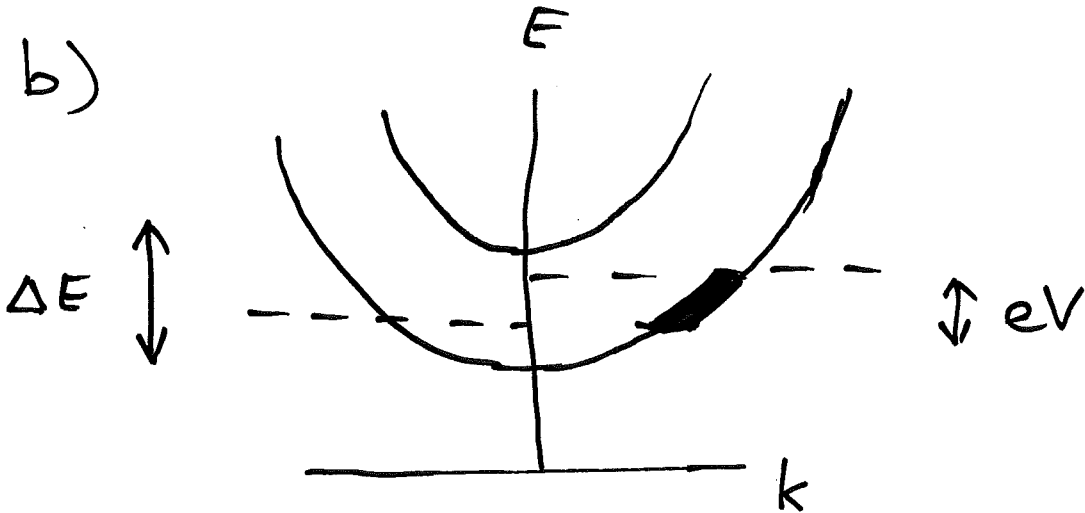
required : $L < \ell_\phi$

$$kT < E_{\text{th}}$$

$$eV < E_{\text{th}}$$

$$E_{\text{th}} = \frac{\hbar D}{L^2} \quad \text{Thouless energy}$$

2 a) see lecture notes



Current carried by states in energy interval eV

required: no additional states occupied/empty in other subbands

→ $eV < \Delta E$
 $kT < \Delta E$

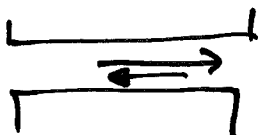
2 c) long/short channel



quantum tunneling possible when L is too short



abrupt channel

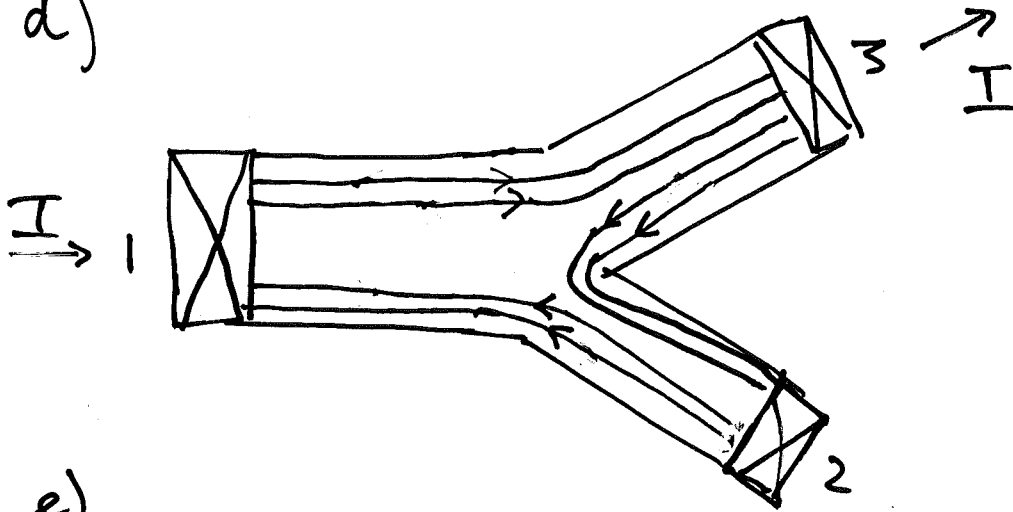


generates reflections at ends
 $T < 1$

(D)

3 a, b, c see exam 17-6-2015

d)



e)

contacts 1 and 3 are current contacts
contact 2 is voltage contact.

→ adjusts the voltage such that
incoming current = outgoing current

$$\begin{array}{ccc} \downarrow & & \downarrow \\ \mu_3 \times \frac{2e^2}{h} \times 2 & & \mu_2 \times \frac{2e^2}{h} \times 2 \\ & \downarrow \text{Spin degeneracy} = 2 & \end{array}$$

therefore: $\mu_3 = \mu_2$ $\mu_3 - \mu_1 = \frac{h}{4e^2} I$

voltage between 1 and 2 = $\frac{h}{4e^2} I$

f) linear system: current reverses
→ voltage reverses sign

g) yes: now $\mu_2 = \mu_1$ $V_{12} = 0$

(E)

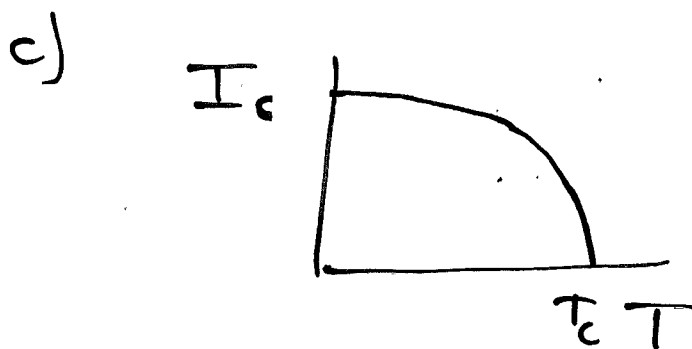
4 a) $I = I_c \sin \varphi$ $I_c = \frac{\pi}{2} \frac{\Delta}{e} G_t$

$$V = \frac{\hbar}{2e} \frac{d\varphi}{dt}$$

Δ : energy gap

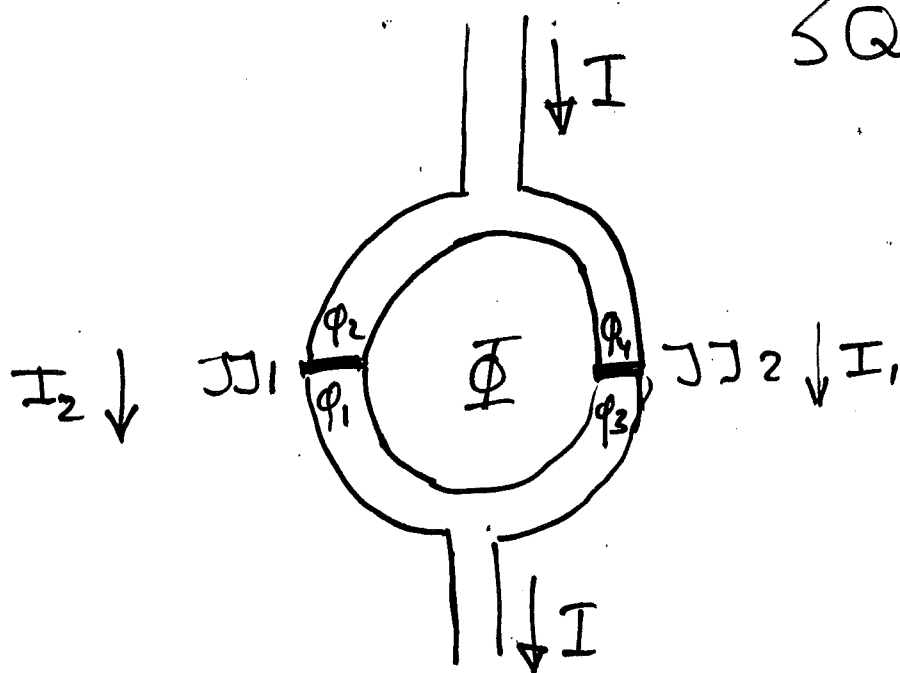
G_t : normal state conductance

b) $V = \frac{\hbar}{2e} \frac{d\varphi}{dt}$ is exact



d)

SQUID



$$I_1 = I_c \sin(\varphi_2 - \varphi_1)$$

$$I_2 = I_c \sin(\varphi_4 - \varphi_3 + \varphi_{AB}) \quad \varphi_{AB} = 2\pi \frac{\Phi}{h/2e}$$

(F)

$$I = I_1 + I_2$$

Assume $I_c \ll$ critical current of superconducting strips \rightarrow

$$\nabla\varphi \text{ in strips} \approx 0 \rightarrow \varphi_1 = \varphi_3 \text{ and } \varphi_2 = \varphi_4$$

$$\Delta\varphi = \varphi_2 - \varphi_1 = \varphi_4 - \varphi_3$$

$$I = I_c \sin(\Delta\varphi) + I_c \sin\left(\Delta\varphi + 2\pi \frac{\Phi}{h/2e}\right)$$

$$= I_c \sin(\Delta\varphi) + I_c \left\{ \sin(\Delta\varphi) \cdot \cos\left(2\pi \frac{\Phi}{h/2e}\right) + \cos(\Delta\varphi) \sin\left(\frac{2\pi\Phi}{h/2e}\right) \right\}$$

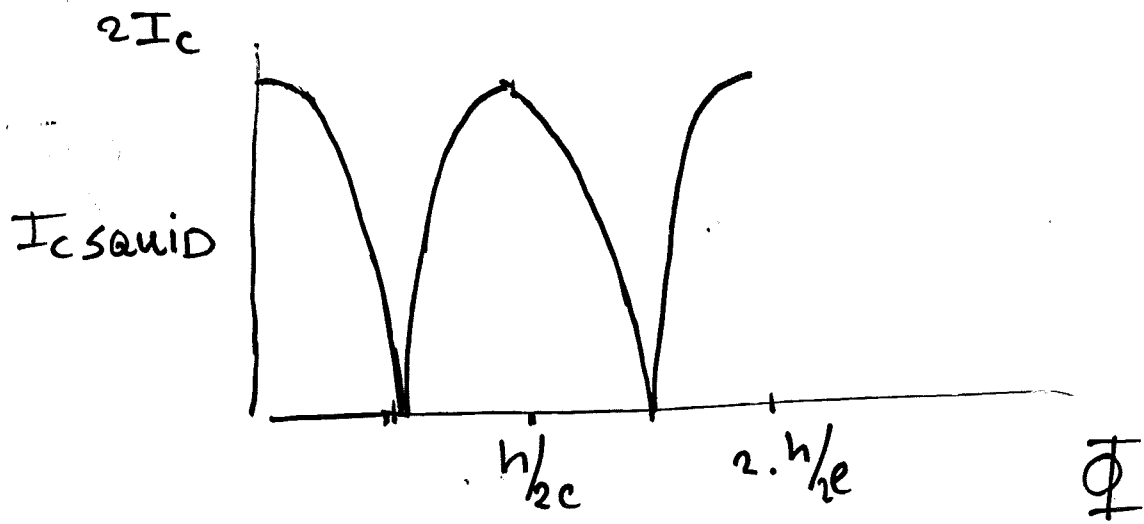
$$= I_c \sin(\Delta\varphi) \left\{ 1 + \cos\left(2\pi \frac{\Phi}{h/2e}\right) \right\} + I_c \cos(\Delta\varphi) \sin\left(\frac{2\pi\Phi}{h/2e}\right)$$

note: Φ is fixed $\Delta\varphi$ is free parameter

$\Delta\varphi$ adjusts itself to maximize I_c squid

$$\frac{I}{I_c \text{ squid}} = \frac{I}{I_c} \sqrt{\left\{ 1 + \cos\left(2\pi \frac{\Phi}{h/2e}\right) \right\}^2 + \sin^2\left(2\pi \frac{\Phi}{h/2e}\right)}$$

$$= I_c \sqrt{2 + 2 \cos\left(2\pi \frac{\Phi}{h/2e}\right)}$$



(6)

Note : $I_{c \text{ squid}} = 2I_c$ for $\Phi = 0, h/2e$ etc.

→ Super currents of JJ add.

$I_{c \text{ squid}} = 0$ for $\Phi = h/4e, 3/4 h/e$ etc

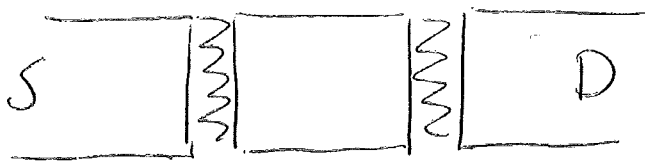
→ Super currents through JJ are always opposite → critical current = 0

5a)

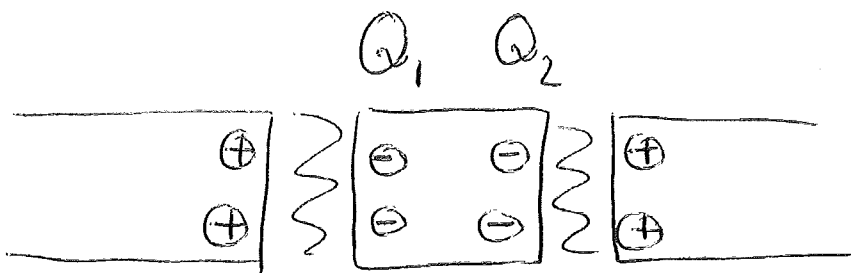
island

SET

(H)

situation 0

neutral island

convention : \ominus or \oplus : $1/4$ electron chargesituation 1 : neutral island
after tunneling of 1 electron

$$\text{Charging energy: } \frac{1}{2} \frac{Q_1^2}{C} + \frac{1}{2} \frac{Q_2^2}{C}$$

$$= \frac{1}{8} \frac{e^2}{C} + \frac{1}{8} \frac{e^2}{C} = \frac{1}{4} \frac{e^2}{C}$$

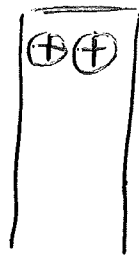
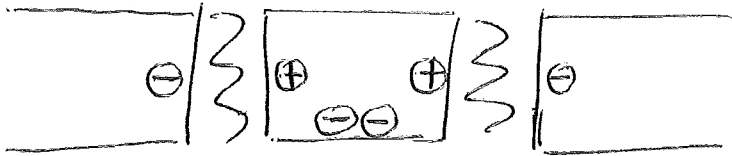
energy change :

$$\Delta E = \frac{1}{4} \frac{e^2}{C} - 0 = \frac{1}{4} \frac{e^2}{C} \rightarrow \text{Coulomb blockade}$$

situation 2 gate bias = $+\frac{1}{2}e$

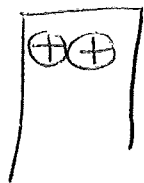
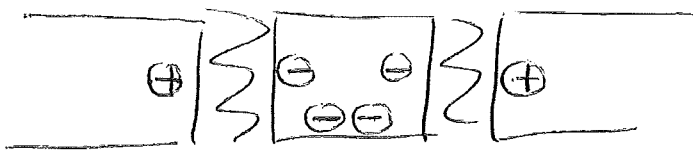


a) before tunneling:



$$\text{charging energy: } \frac{1}{2} \frac{\left(\frac{1}{4}e\right)^2}{C} + \frac{1}{2} \frac{\left(\frac{1}{4}e\right)^2}{C} = \frac{1}{16} \frac{e^2}{C}$$

b) after tunneling

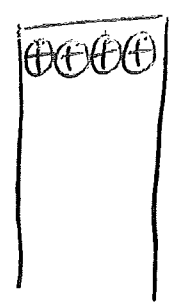
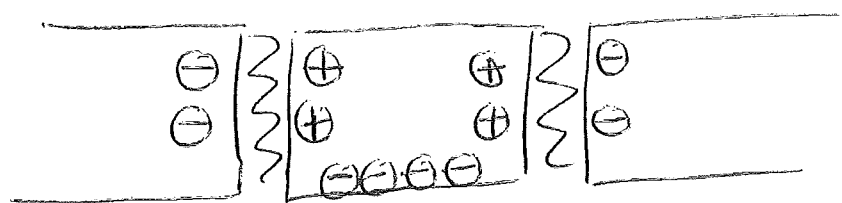


charging energy the same \rightarrow No Coulomb blockade

5

Situation 3

gate bias = +1e



the system minimizes its charging energy by the tunneling of an electron
→ back to situation 0

5 b)

$$kT < \Delta E$$

$$\Delta E \approx \frac{e^2}{C}$$

(K)

$$V_{DS} < \frac{\Delta E}{e}$$

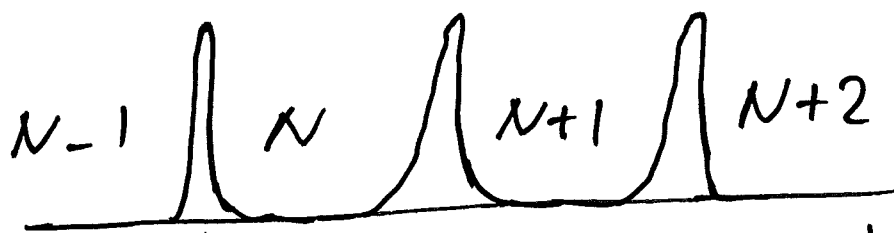
V_{DS} : source-drain voltage

$$R > \frac{e^2}{h}$$

tunnel resistance has to be larger than typically e^2/h

5 c) see above

5 d)



SET conductance peaks when V_g
charging energy for N and $N+1$ electrons
on the island is the same

at low π Coulomb blockade becomes already
effective for small deviations from the
above condition \rightarrow

sharp conductance peaks as function of V_g

\rightarrow SET can measure very small
($< 10^{-4}e$) changes in charge environment.